

Form 1449\*

Atty. Docket No.: 303.648US1

Serial No. 09/484,303

## INFORMATION DISCLOSURE STATEMENT

BY APPLICANT

(Use several sheets if necessary)

Applicant: Kië Y. Ahn et al.

Filing Date: January 18, 2000

Group: 2825

JUL 12 2000

## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>NB</i>	2,842,438 ✓	07/08/1958	Saarivirta, M.J., et al.	75	153	08/02/56
<i>NB</i>	3,954,570 ✓	06/04/1976	Shirk, et al.	201	15	11/11/74
<i>NB</i>	4,386,116 ✓	05/31/1983	Nair, et al.	427	99	12/24/81
<i>NB</i>	4,423,547 ✓	01/03/1984	Farrar, P.A., et al.	29	571	06/01/81
<i>NB</i>	4,574,095 ✓	03/04/1986	Baum, et al.	427	53.1	11/19/84
<i>NB</i>	4,762,728 ✓	08/09/1988	Keyser, T., et al.	427	38	11/26/85
<i>NB</i>	4,788,082 ✓	11/29/1988	Schmitt	427	248.1	12/12/85
<i>NB</i>	4,931,410 ✓	06/05/1990	Tokunaga, et al.	437	189	08/25/88
<i>NB</i>	4,962,058 ✓	10/09/1990	Cronin, J.E., et al.	437	187	04/14/89
<i>NB</i>	4,996,584 ✓	02/26/1991	Young, P.L., et al.	357	71	10/13/88
<i>NB</i>	5,019,531 ✓	05/28/1991	Awaya, N., et al.	437	180	05/19/89
<i>NB</i>	5,100,499 ✓	03/31/1992	Douglas, M.A.	156	635	06/25/91
<i>NB</i>	5,130,274 ✓	07/14/1992	Harper, J.M., et al.	437	195	04/05/91
<i>NB</i>	5,158,986 ✓	10/27/1992	Cha, S.W., et al.	521	82	04/05/91
<i>NB</i>	5,173,442 ✓	12/22/1992	Carey, D.H.	437	173	03/24/92
<i>NB</i>	5,240,878 ✓	08/31/1993	Fitzsimmons, J.A., et al.	437	187	04/26/91
<i>NB</i>	5,243,222 ✓	09/07/1993	Harper, J.M., et al.	257	774	01/08/92
<i>NB</i>	5,256,205 ✓	10/26/1993	Schmitt, III, et al.	118	723	01/07/92
<i>NB</i>	5,334,356 ✓	08/02/1994	Baldwin, D.F., et al.	422	133	08/24/92
<i>NB</i>	5,354,712 ✓	10/11/1994	Ho, Y.Q., et al.	437	195	11/12/92
<i>NB</i>	5,426,330 ✓	06/20/1995	Joshi, R.V., et al.	257	752	09/21/93
<i>NB</i>	5,442,237 ✓	08/15/1995	Hughes, H.G., et al.	257	759	02/04/94
<i>NB</i>	5,470,789 ✓	11/28/1995	Misawa, N.	437	190	03/07/95
<i>NB</i>	5,470,801 ✓	11/28/1995	Kapoor, et al.	437	238	06/28/93
<i>NB</i>	5,506,449 ✓	04/09/1996	Nakano, et al.	257	758	03/23/94
<i>NB</i>	5,538,922 ✓	07/23/1996	Cooper, K.J., et al.	437	195	01/25/95
<i>NB</i>	5,635,253 ✓	06/03/1997	Canaperi, et al.	427	437	06/07/95
<i>NB</i>	5,674,787 ✓	10/07/1997	Zhao, et al.	437	230	01/16/96
<i>NB</i>	5,679,608 ✓	10/21/1997	Cheung, et al.	437	195	06/05/95
<i>NB</i>	5,681,441 ✓	10/28/1997	Svendsen, et al.	205	114	12/22/92
<i>NB</i>	5,695,810 ✓	12/09/1997	Dubin, et al.	427	96	11/20/96
<i>NB</i>	5,739,579 ✓	04/14/1998	Chiang, C., et al.	257	635	09/10/96
<i>NB</i>	5,780,358 ✓	07/14/1998	Zhou, M.S.	438	645	04/08/96
<i>NB</i>	5,785,570 ✓	07/28/1998	Bruni, M.D.	445	52	07/25/95
<i>NB</i>	5,792,522 ✓	08/11/1998	Jin, S., et al.	427	575	09/18/96
<i>NB</i>	5,801,098 ✓	09/01/1998	Fiordalice, R., et al.	438	653	09/03/96
<i>NB</i>	5,891,797 ✓	04/06/1999	Farrar, P.A.	438	619	10/20/97
<i>NB</i>	5,891,804 ✓	04/06/1999	Havemann, R.H., et al.	438	674	04/14/97

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*Neal Berermy*

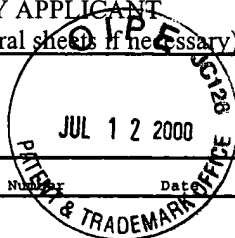
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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>NB</i>	5,897,370 ✓	04/27/1999	Joshi, R.V., et al.	438	632	10/28/96
<i>NB</i>	5,911,113 ✓	06/08/1999	Yao, G., et al.	438	649	03/18/97
<i>NB</i>	5,932,928 ✓	08/03/1999	Clampitt, D.A.	257	758	07/03/97
<i>NB</i>	5,972,804 ✓	10/26/1999	Tobin, P.J., et al.	438	786	11/03/97
<i>NB</i>	5,981,350 ✓	11/09/1999	Geusic, J.E., et al.	438	386	05/29/98
<i>NB</i>	5,985,759 ✓	11/16/1999	Kim, E., et al.	438	653	02/24/98
<i>NB</i>	5,994,777 ✓	11/30/1999	Farrar, P.A.	257	758	08/26/98
<i>NB</i>	6,008,117 ✓	12/28/1999	Hong, Q., et al.	438	629	03/19/97
<i>NB</i>	6,030,877 ✓	02/29/2000	Lee, C., et al.	438	381	10/06/97

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
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<i>NB</i>	In: <u>Kirk-Othmer Concise Encyclopedia of Chemical Technology</u> , Grayson, M., (ed.), John Wiley & Sons, Inc., New York, NY, p. 433-435, 926-938, (1985) ✓
<i>NB</i>	In: <u>Metals Handbook, Ninth Edition, Vol. 2, Properties and Selection: Nonferrous Alloys and Pure Metals</u> , ASM Handbook Committee, (eds.), American Society for Metals, Metals Park, OH, 157, 395, (1989) ✓
<i>NB</i>	"Brooks Model 5964 High Performance Metal Seal Mass Flow Controller (Introduced in 1991)", <u>Brooks Instrument</u> , <a href="http://www.frco.com/brooks/semiconductor/products1i.html">http://www.frco.com/brooks/semiconductor/products1i.html</a> , 1 page, (1991) ✓
<i>NB</i>	Abe, K., et al., "Sub-half Micron Copper Interconnects Using Reflow of Sputtered Copper Films", <u>VLSI Multilevel Interconnection Conference</u> , 308-311, (June 25-27, 1995) ✓
<i>NB</i>	Andricacos, P.C., "Copper On-Chip Interconnections", <u>The Electrochemical Society Interface</u> , pp. 32-37, (1999) ✓
<i>NB</i>	Anonymous, "Formation of Conductors at Variable Depths -- Using Differential Photomask, Projecting Images into Insulator by Reactive Ion Etching, Selectively Filling Images with Conductor", <u>Research Disclosure</u> , Disclosure No. RD 291015, Abstract, 1 p., (July 10, 1988) ✓
<i>NB</i>	Anonymous, "Improved Metallurgy for Wiring Very Large Scale Integrated Circuits", <u>International Technology Disclosures</u> , 4, Abstract, 1 page, (1986) ✓

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NB	Ding, et al., "Copper Barrier, Seed Layer and Planerization Technologies", <u>VMIC Conference Proceedings</u> , pp. 87-92, (1997) ✓
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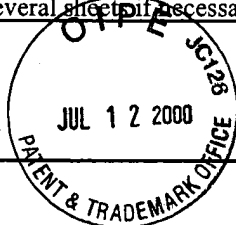
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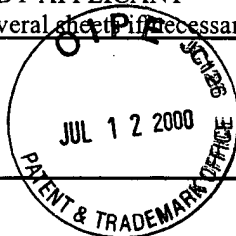
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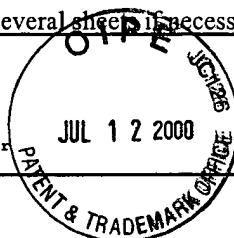
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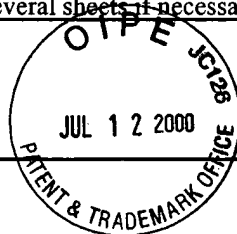
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(Including Author, Title, Date, Pertinent Pages, Etc.)

NB	Winters, H.F., et al., "Influence of Surface Absorption Characteristics on Reactivity Sputtered Films Grown in the Biased and Unbiased Modes", <u>J. Appl. Phys.</u> , 43(3), pp. 794-799, (1972) ✓
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